

Young Dong Kim

List of Publications by Year in descending order

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43
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602
citing authors

#	ARTICLE	IF	CITATIONS
1	Azimuthal angle dependent dielectric function of SnS by ellipsometry. Journal of the Korean Physical Society, 2022, 80, 59-62.	0.7	0
2	A Systematic Study of Compositionally Dependent Dielectric Tensors of SnS _x Se _{1-x} Alloys by Spectroscopic Ellipsometry. Crystals, 2021, 11, 548.	2.2	3
3	Temperature dependence of the dielectric function and critical points of $\hat{\epsilon}$ -SnS from 27 to 350ÅK. Scientific Reports, 2020, 10, 18396.	3.3	11
4	Temperature dependence of optical properties of monolayer WS ₂ by spectroscopic ellipsometry. Applied Surface Science, 2020, 511, 145503.	6.1	21
5	A Parametric Model for Temperature Dependence of Dielectric Function of AlSb Film. Journal of Nanoscience and Nanotechnology, 2019, 19, 6801-6807.	0.9	0
6	Characterization of wafer-scale MoS ₂ and WSe ₂ 2D films by spectroscopic ellipsometry. Current Applied Physics, 2017, 17, 1329-1334.	2.4	26
7	Temperature dependence of the critical points of monolayer MoS ₂ by ellipsometry. Applied Spectroscopy Reviews, 2016, 51, 621-635.	6.7	27
8	Parameterization of the dielectric function of In _x Al _{1-x} As alloys as a function of composition. Current Applied Physics, 2015, 15, S30-S34.	2.4	5
9	Pressure dependence of effective dynamic charge in In _x Al _{1-x} As ternary alloys. Solid State Communications, 2015, 221, 41-44.	1.9	0
10	Analytic representation of the dielectric function of GaN for temperatures from 26 to 690 K. Journal of the Korean Physical Society, 2014, 65, 733-738.	0.7	2
11	Ellipsometric study of the temperature dependences of the dielectric function and the critical points of AlSb at temperatures from 300 to 803 K. Journal of the Korean Physical Society, 2014, 65, 515-519.	0.7	1
12	Analytic determination of the dielectric function of InSb at energies from 0.74 to 6.42 eV at temperatures from 31 to 675 K. Journal of the Korean Physical Society, 2014, 64, 1872-1877.	0.7	1
13	Temperature dependent dielectric function and the E_c critical points of hexagonal GaN from 30 to 690 K. AIP Advances, 2014, 4, .	1.3	7
14	Reinforcement of Interfacial Adhesion of a Coated Polymer Layer on a Cobalt-Chromium Surface for Drug-Eluting Stents. Langmuir, 2014, 30, 8020-8028.	3.5	20
15	Effect of post-annealing temperature on the dielectric function of solution-processed LaAlO ₃ /Si Films. Journal of the Korean Physical Society, 2014, 64, 1509-1513.	0.7	0
16	Parameterization of the dielectric functions of InGaSb alloys. Current Applied Physics, 2014, 14, 768-771.	2.4	2
17	Influences of rapid thermal process on solution-deposited Ti-silicate/Si films: Phase segregation, composition and interface changes, and dielectric properties. Materials Chemistry and Physics, 2014, 145, 168-175.	4.0	6
18	Effect of different sputtering gas mixtures on the structural, electrical, and optical properties of p-type NiO thin films. Materials Science in Semiconductor Processing, 2013, 16, 1346-1351.	4.0	16

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19	Application of rapid thermal process to solution-processed Ti-silicate films for enhancing permittivity without losing amorphous nature. <i>Current Applied Physics</i> , 2013, 13, S41-S44.	2.4	2
20	Optical properties and photo-oxidative degradation of regioregular poly(3-butylthiophene) films by spectroscopic ellipsometry. <i>Thin Solid Films</i> , 2013, 542, 338-342.	1.8	3
21	Temperature dependence of the dielectric functions and the critical points of InSb by spectroscopic ellipsometry from 31 to 675 K. <i>Journal of Applied Physics</i> , 2013, 114, .	2.5	15
22	Parameterization of the dielectric function of InP from 1.19 to 6.57 eV for temperatures from 25 to 700 K. <i>Journal of Applied Physics</i> , 2012, 112, .	2.5	6
23	Parametric model dielectric functions of InAs for temperatures from 22 to 675 K. <i>Journal of the Korean Physical Society</i> , 2012, 61, 1821-1825.	0.7	4
24	Investigation of InSb critical-point energies at 25 K by using spectroscopic ellipsometry. <i>Journal of the Korean Physical Society</i> , 2012, 61, 439-443.	0.7	1
25	Dielectric function and energy of the E ₀ critical point of hexagonal GaN at 26 K studied by using spectroscopic ellipsometry. <i>Journal of the Korean Physical Society</i> , 2012, 61, 791-794.	0.7	2
26	Temperature dependence of the dielectric function and critical-point energies of InAs. <i>Journal of the Korean Physical Society</i> , 2012, 61, 97-101.	0.7	6
27	Pressure-induced variation of effective dynamic charge in InP _{1-x} As _x alloys due to charge transfer within cation sublattice. <i>Solid State Communications</i> , 2012, 152, 2177-2180.	1.9	1
28	Optical Study of Mn-Doped Bi ₄ Ti ₃ O ₁₂ Thin Films by Spectroscopic Ellipsometry. <i>Journal of Nanoscience and Nanotechnology</i> , 2011, 11, 884-888.	0.9	2
29	Effect of annealing temperature on microstructural evolution and electrical properties of sol-gel processed ZrO ₂ /Si films. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	54
30	Study of the Interaction Between Biomolecule Monolayers Using Total Internal Reflection Ellipsometry. <i>Journal of the Korean Physical Society</i> , 2011, 58, 1031-1034.	0.7	8
31	Effect of the Ga Ratio on the Dielectric Function of Solution-processed InGaZnO Films. <i>Journal of the Korean Physical Society</i> , 2011, 59, 3396-3400.	0.7	4
32	In-situ study of molecular dynamics in a water environment by using imaging ellipsometry. <i>Advances in Natural Sciences: Nanoscience and Nanotechnology</i> , 2010, 1, 045003.	1.5	0
33	InAs critical-point energies at 22 K from spectroscopic ellipsometry. <i>Applied Physics Letters</i> , 2010, 97, 171912.	3.3	21
34	Imaging of Collapsed Fatty Acid Films at Air-Water Interfaces. <i>Langmuir</i> , 2009, 25, 9262-9269.	3.5	22
35	Direct Imaging of a Collapsed Langmuir Monolayer and Multilayer Formation. <i>Journal of the Korean Physical Society</i> , 2008, 53, 1488-1491.	0.7	1
36	Optical Properties of GaN by Using Ellipsometry and a Band Calculation. <i>Journal of the Korean Physical Society</i> , 2008, 53, 1575-1579.	0.7	10

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37	Precision auto-alignment for incident angle of an ellipsometer using specimen stage. <i>Thin Solid Films</i> , 2004, 455-456, 72-77.	1.8	0
38	Precision auto-alignment for the specimen stage of an ellipsometer. <i>Review of Scientific Instruments</i> , 2002, 73, 2988-2993.	1.3	1
39	In situ analysis of surface photoabsorption spectra during InP ALE in metal organic chemical vapor deposition. <i>Microelectronic Engineering</i> , 2000, 51-52, 43-50.	2.4	5
40	Effects of growth interruption on the evolution of InAs/InP self-assembled quantum dots. <i>Journal of Electronic Materials</i> , 2000, 29, 535-541.	2.2	15
41	Analysis of P adsorption and desorption on the (001) InP surface using surface photoabsorption. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1999, 17, 2663-2667.	2.1	9
42	Shape change of InAs self-assembled quantum dots induced by As/P exchange reaction. <i>Thin Solid Films</i> , 1999, 357, 81-84.	1.8	11
43	Effects of As/P exchange reaction on the formation of InAs/InP quantum dots. <i>Applied Physics Letters</i> , 1999, 74, 2029-2031.	3.3	113